

IV. AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method for manufacturing an SOI wafer comprising the steps of:

providing two starting wafers with each starting wafer having at least one line-defect-free surface;

forming an insulating layer on the line-defect-free surface on at least one wafer of two starting wafers; and

adhering the one wafer to the other wafer without an adhesive with the line-defect-free surfaces facing each other;

~~wherein there is used as the starting wafer a wafer having no line defect on a surface thereof.~~

2. (Currently Amended) A method for manufacturing an SOI wafer comprising the steps of:

forming an insulating layer on at least one wafer of the two starting wafers; and

adhering the one wafer to the other wafer without an adhesive,

wherein the starting wafer is subjected to high temperature heat treatment in advance and

wherein the high temperature heat treatment is carried out at a high temperature of 1100°C or higher for at least one hour.

3. (Canceled)

4. (Previously Presented) The method for manufacturing an SOI wafer according to claim 1, wherein the method comprises the steps of:

forming an insulating layer on at least one wafer of the two starting wafers;

implanting hydrogen ions or rare gas ions through the upper surface of the one wafer to form a micro-bubble layer in the interior of the one wafer; thereafter

bringing the surface of the one wafer through which the ions have been implanted into close contact with the other wafer through the insulating layer interposed therebetween; then

delaminating a part of the one wafer with the micro-bubble layer as a cleavage plane by applying heat treatment for the rest thereof to become a thin film; and

bonding strongly the one wafer in the form of a thin film to the other wafer through the insulating layer interposed therebetween by applying further heat treatment.

5. (Previously Presented) The method for manufacturing an SOI wafer according to claim 1, wherein surfaces of wafers each to be used as the starting wafer of the SOI wafer are inspected with respect of a line defect to sort line defect free wafers for use.

6. (Original) The method for manufacturing an SOI wafer according to claim 5, wherein the inspection of the line defect is carried out with a laser microscope with a confocal optical system.